

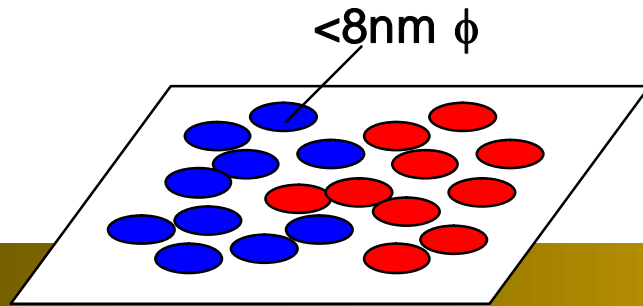
TOSHIBA

Leading Innovation >>>

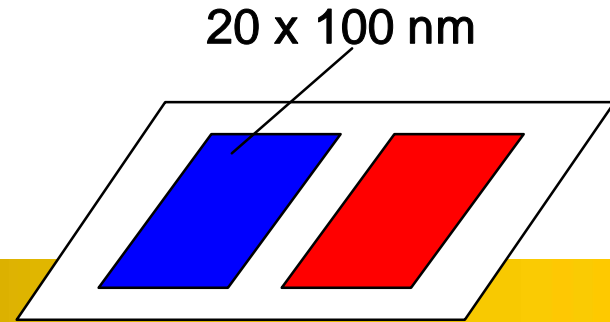
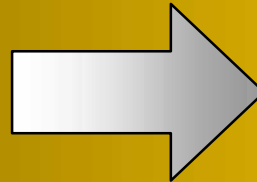
X線反射率法を用いたパターン媒体の 加工ダメージ評価

(株)東芝 研究開発センター
喜々津 哲

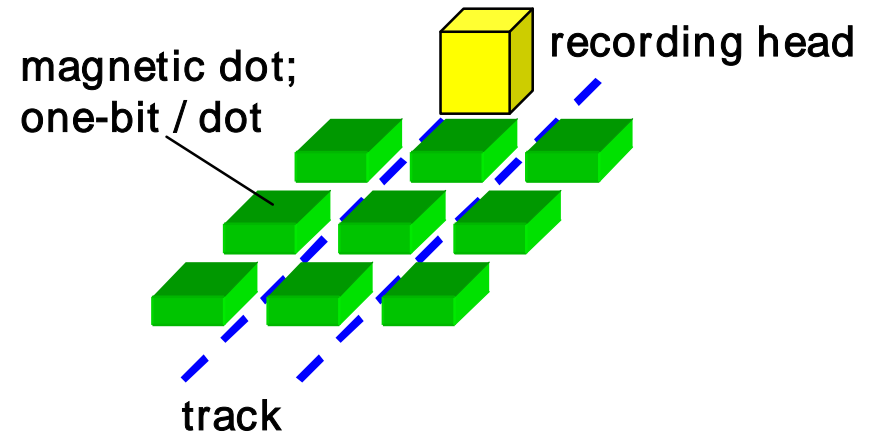
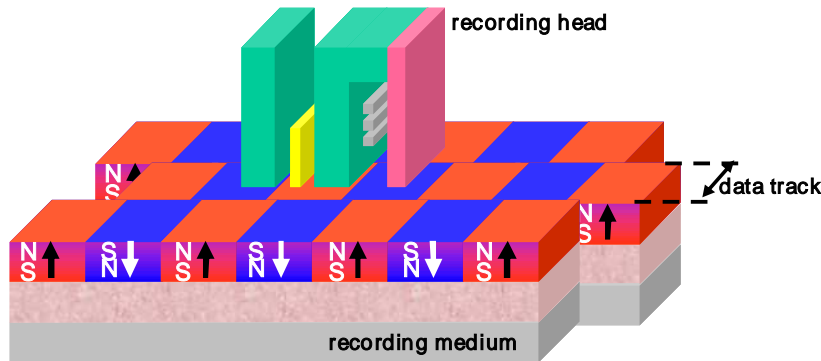
パターンド媒体のコンセプト



現行媒体:
微小磁性粒子による
の熱揺らぎ問題



パターンド媒体:
連続膜をビットサイズに加工
V大 熱揺らぎ回避



パターンド媒体の課題

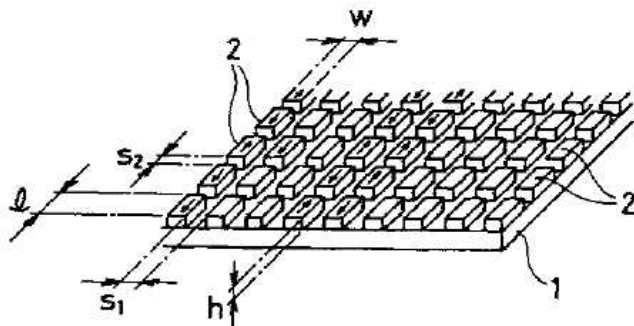
Challenging Issues

- 製造(加工)方法
- 浮上性能/表面平滑化

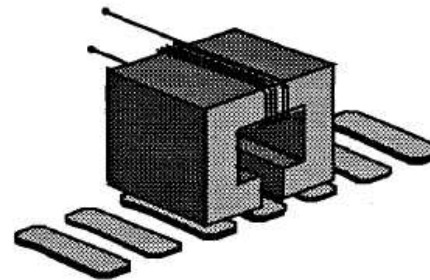
feature size~10nm

Engineering Issues

- 媒体の磁気特性デザイン
- サーボ、ヘッド位置制御法
- 信号制御、チャンネル (ビットに同期した記録)
- ヘッドデザイン



Nakatani: Japanese Pat. (1989)



R. White: IEEE Trans. Magn., 33 p.990 (1997)

ポリマーの自己組織化を利用した微細パターン

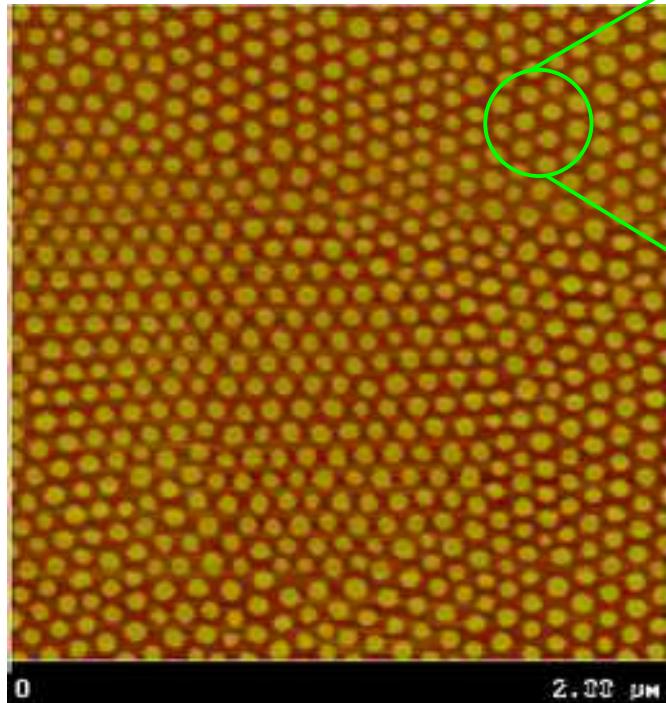
PS-PMMA ジブロックコポリマー (di-block co-polymer)

ポリスチレン (PS)
(分子量: 172000)

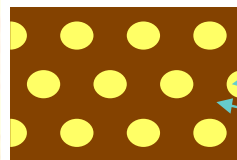
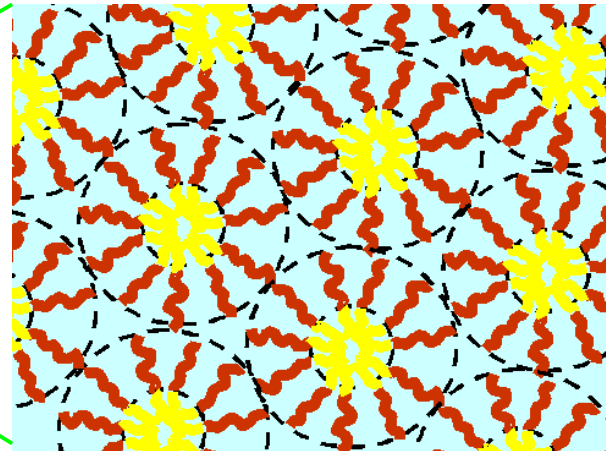


ポリメチルメタクリレート (PMMA)
(分子量: 41500)

AFM 位相像



80 nm 間隔, 40nm 直径



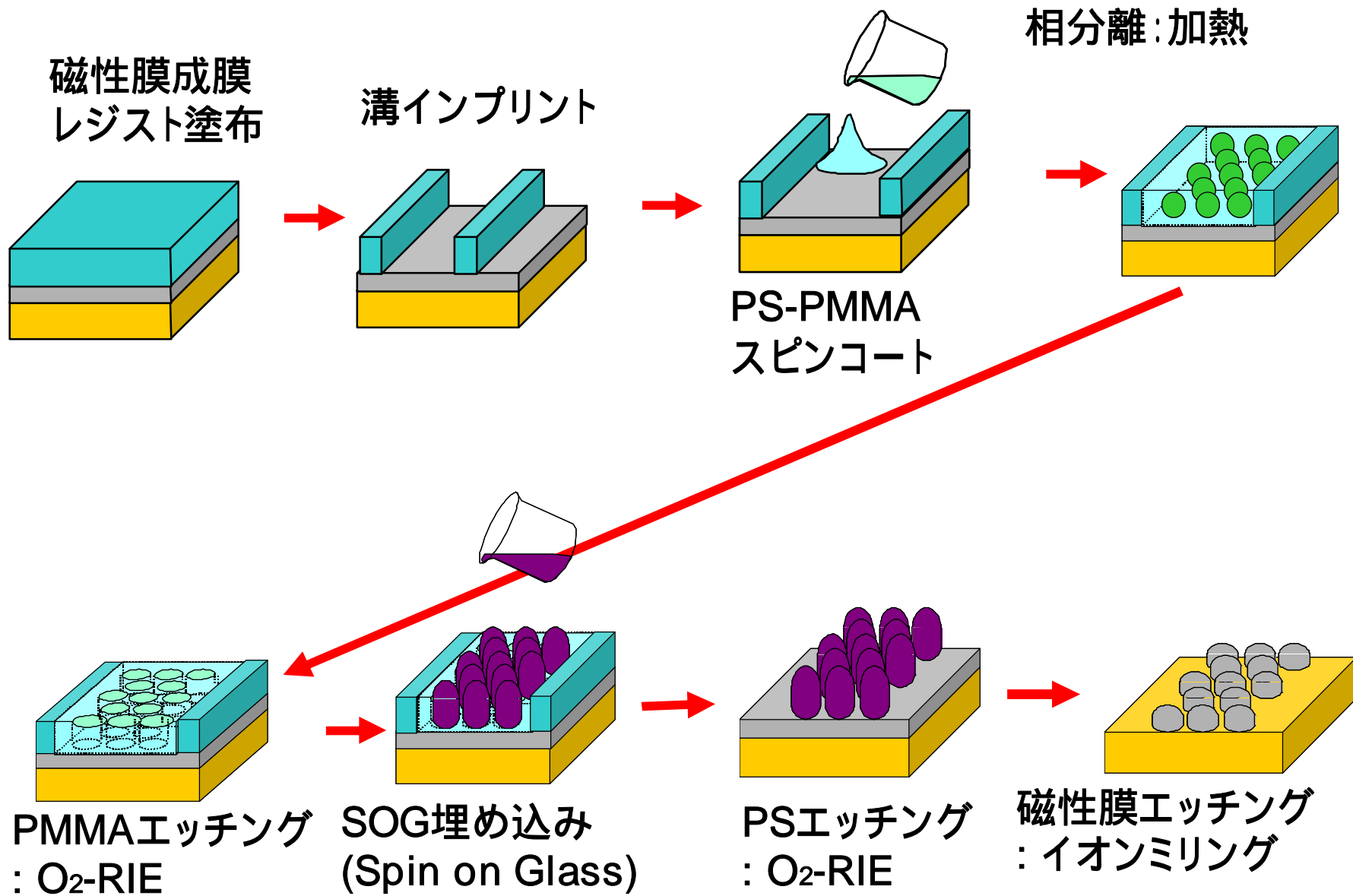
PMMA

PS

自己組織化

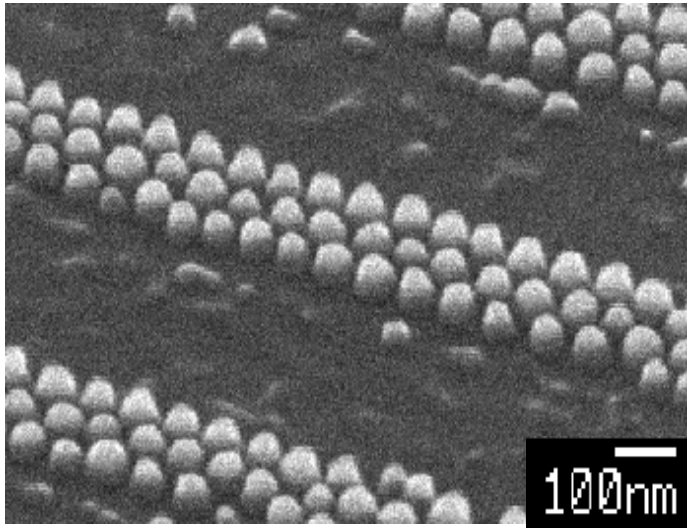
- ・大面積のナノ構造を一度に形成
- ・~10nmも可

パターンド媒体形成プロセス



CoCrPtパターンメディア

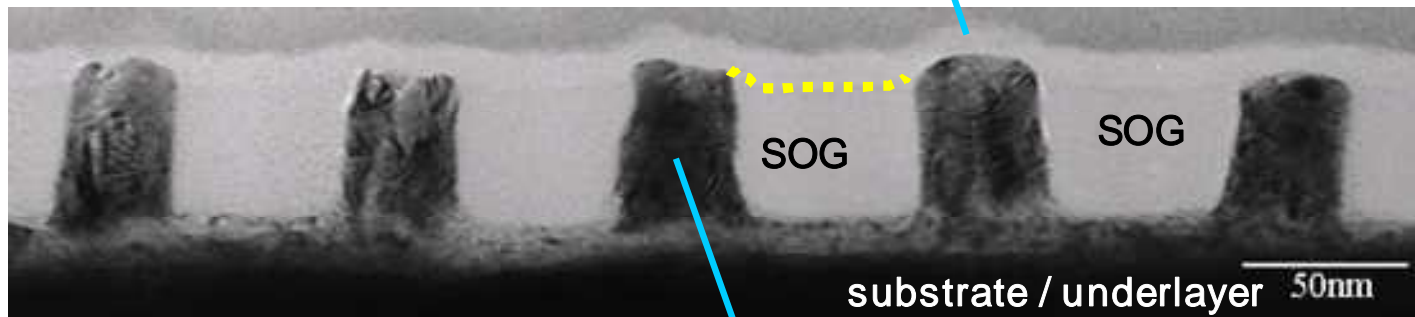
Co₇₄Cr₆Pt₂₀パターンメディア(80 nmピッチ、40 nm直径)



SEM像



全体像

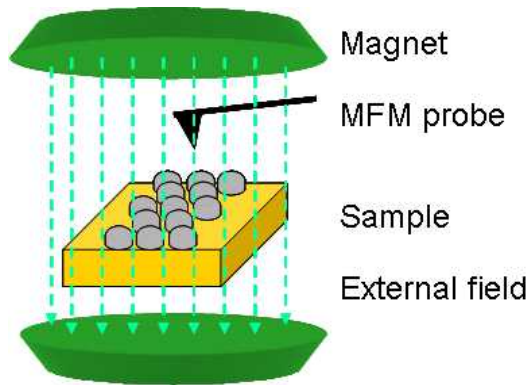


C保護膜

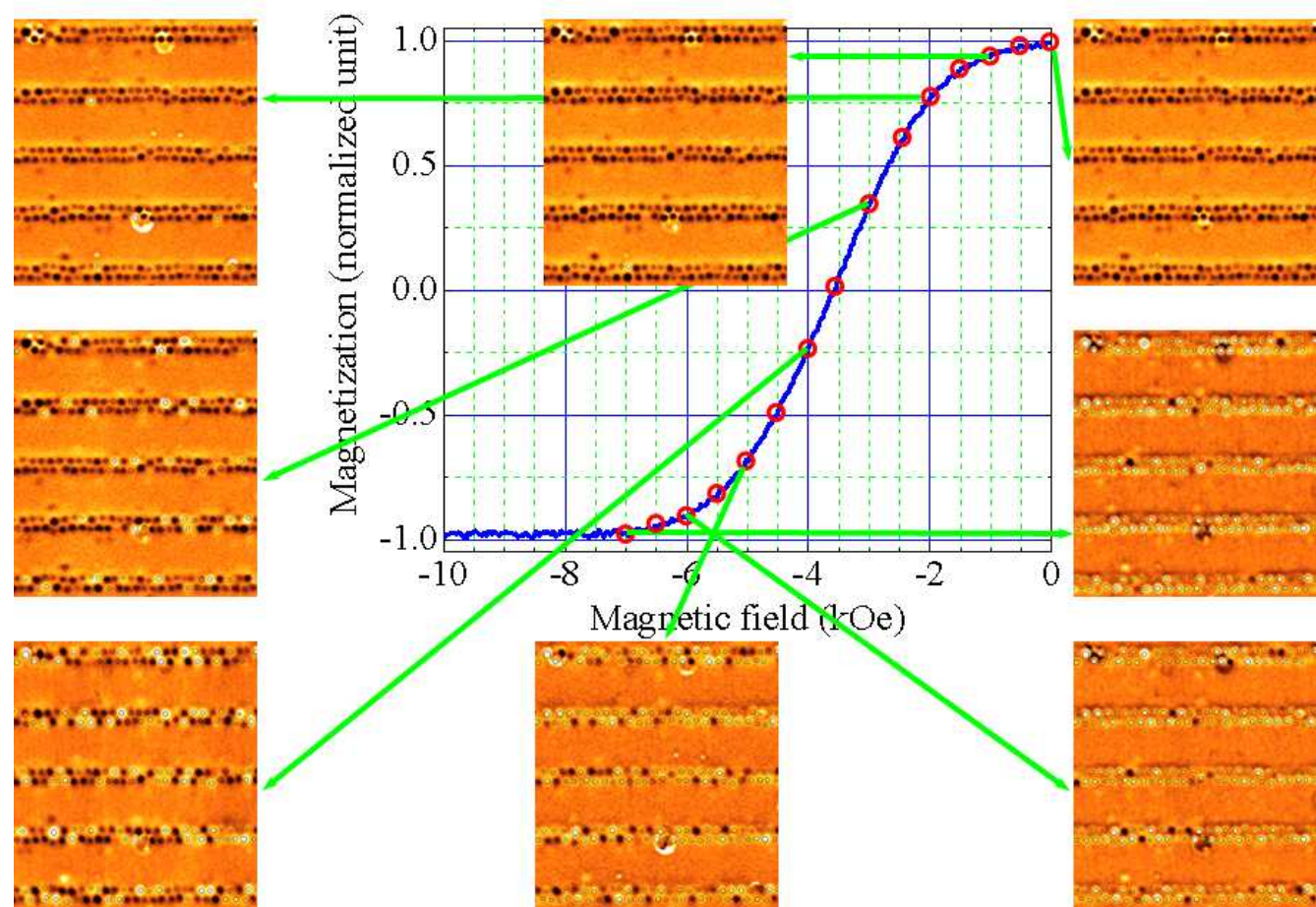
CoCrPt

Y. Kamata: Intermag06 GE-09

MFMを使ったドット毎の磁気特性測定



磁界印加 MFM測定



反転したドット個数を数える = 磁化量

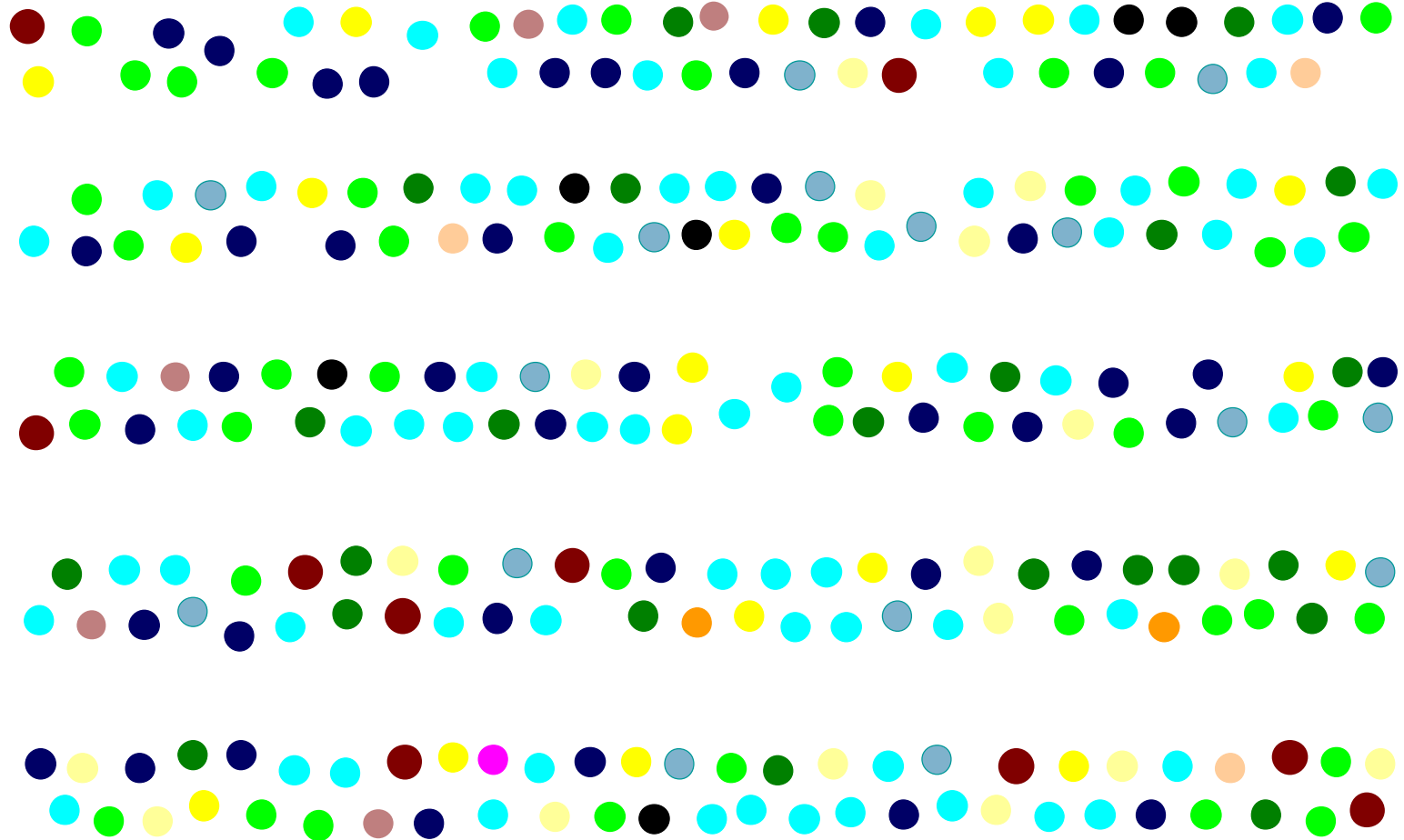
J.Bai et al., J. Appl. Phys., Vol.96, No.2, 1133(2004).

各ドットの保磁力分布

Hc distribution of aligned CoCrPt dots (40nm ϕ)

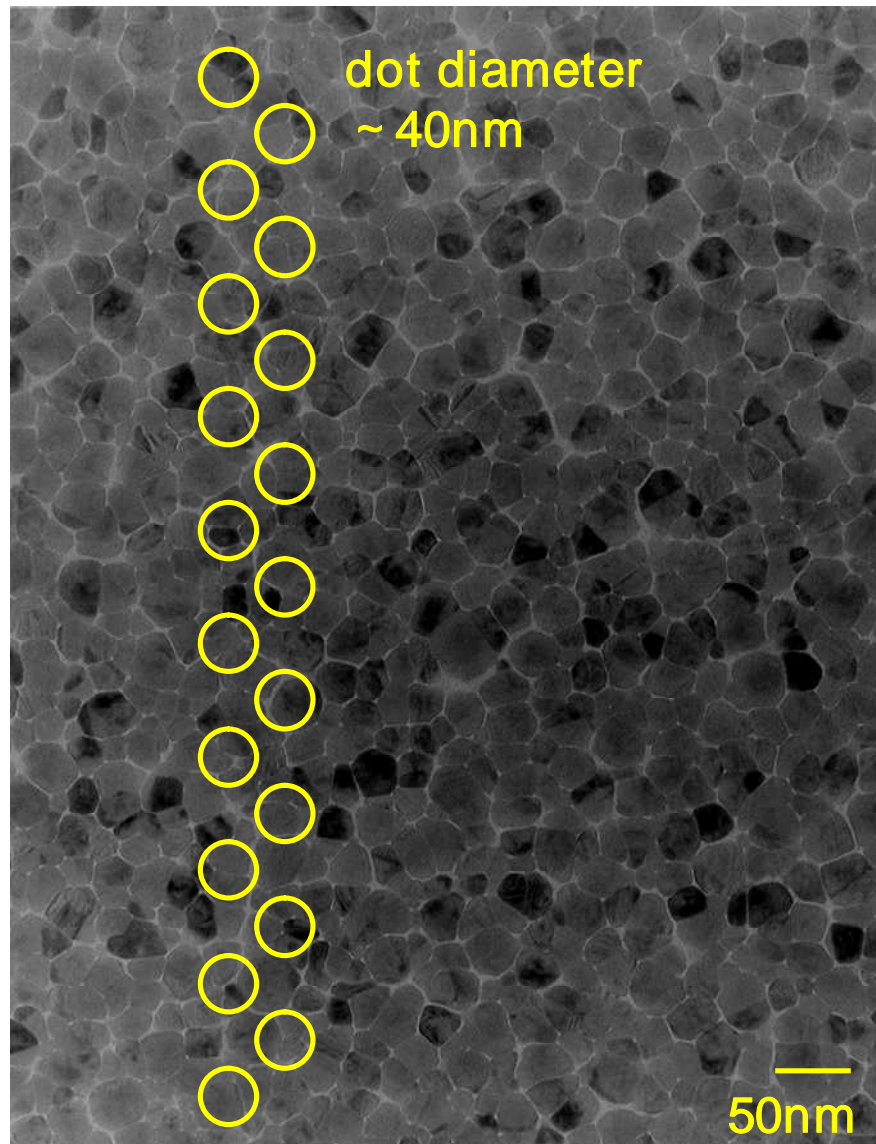
H_c

- 0 – 0.5
- 0.5 – 1.0
- 1.0 – 1.5
- 1.5 – 2.0
- 2.0 – 2.5
- 2.5 – 3.0
- 3.0 – 3.5
- 3.5 – 4.0
- 4.0 – 4.5
- 4.5 – 5.0
- 5.0 – 5.5
- 5.5 – 6.0
- 6.0 – 6.5
- > 6.5

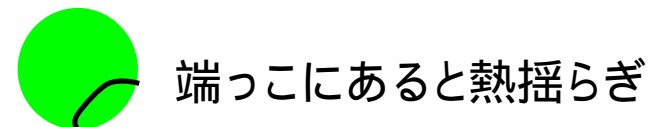
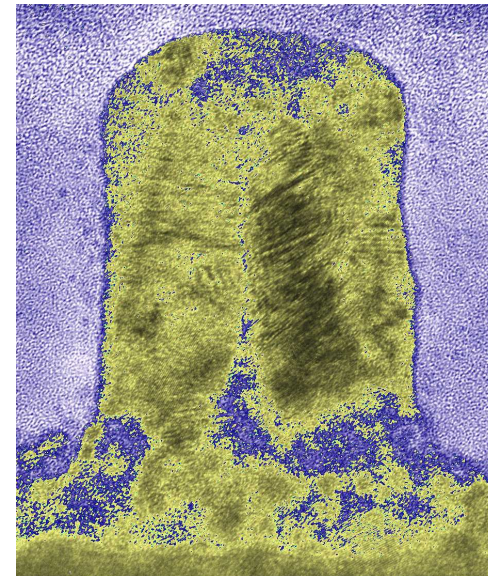


Y. Kamata: Intermag 06 GE-09

ドットの均一性：数本の粒界、異方性軸分布

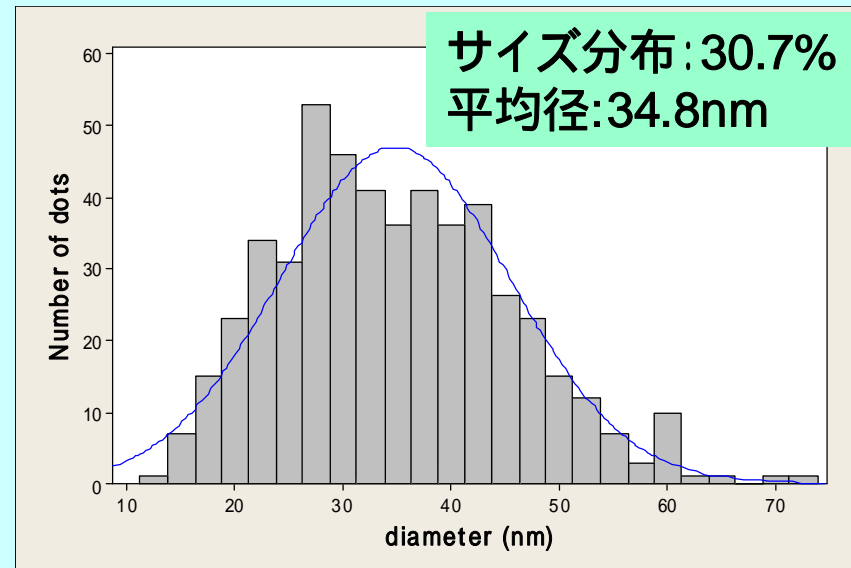
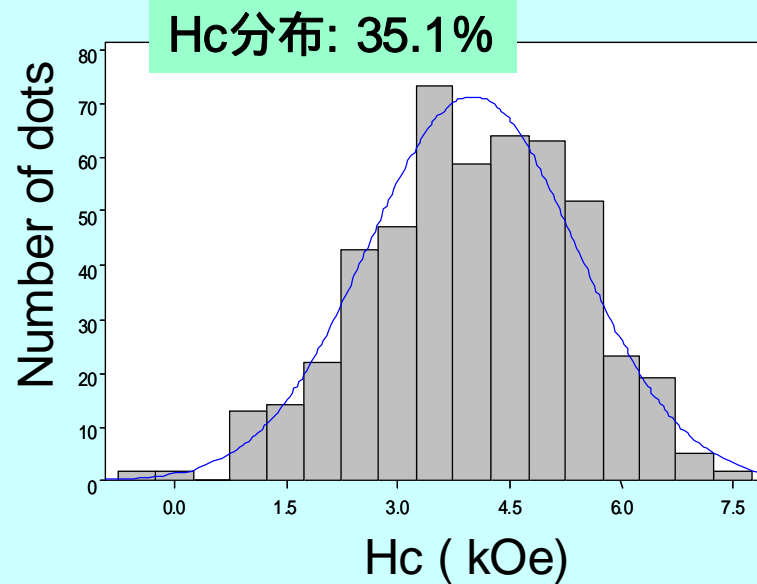


磁性膜の平均粒径: 22.9 nm
パターンサイズ: 40 nm
ドット中に粒界が1-2個



垂直配向軸のばらつき、

磁気特性分布の原因



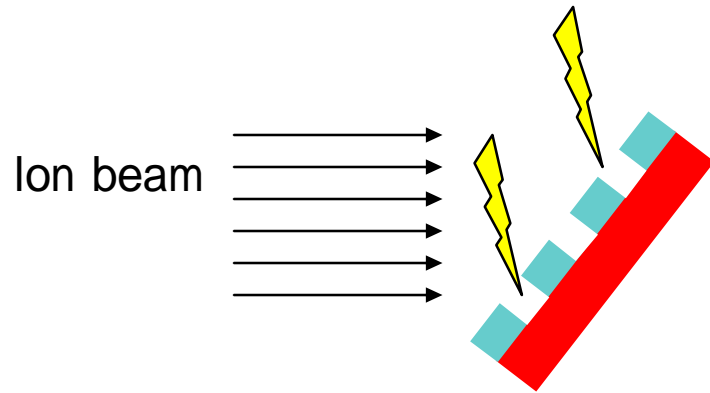
Y. Kamata: JJAP Vol.40, No.3A, 999(2007)

possible origin of the distribution

- dot size distribution
- microscopic composition dispersion
- grain boundary
- **damage by the etching process**
... TEM, simulation: little damage by ion milling

Ar イオンミリングプロセス

利点: どのような磁性膜でもエッチングできる
欠点: エッチングダメージ

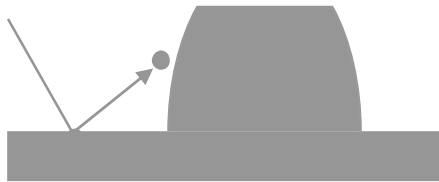


ダメージ

- ・垂直磁気異方性の劣化
- ・結晶性劣化
- ・ドット形状の破壊

redeposition: 再付着

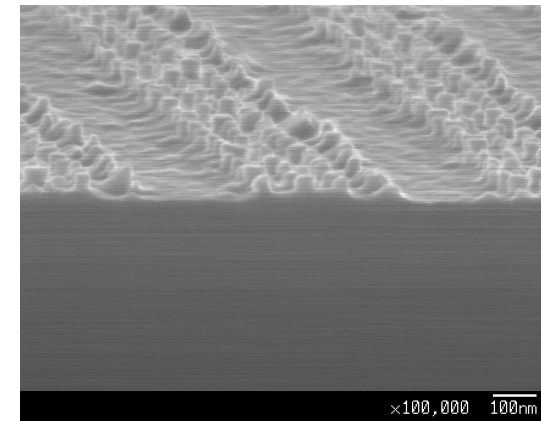
Ion beam



Back sputtering

sidewall etching: サイドエッチ

Ion beam

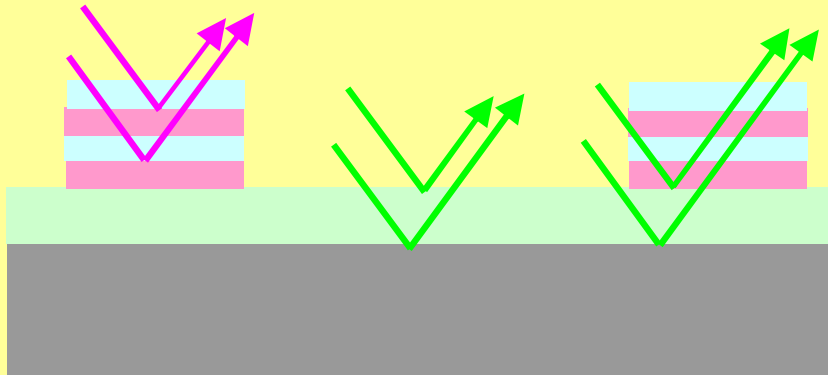


introduction (II)

motivation:

etching damage analysis of the patterned media
made by ion milling process with self assembled mask

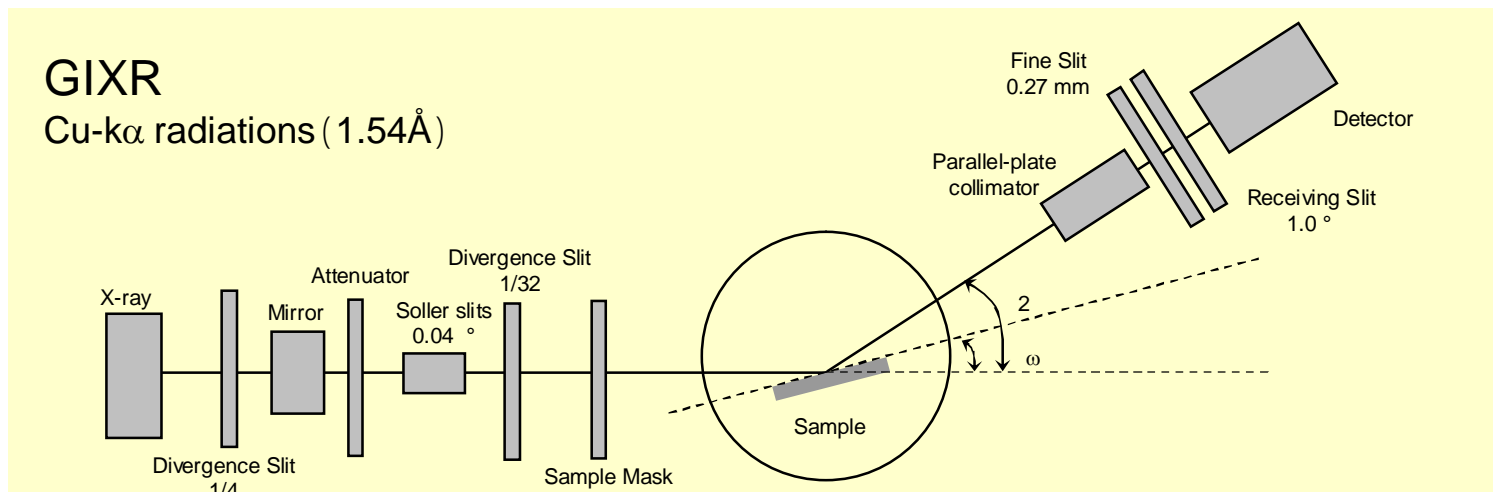
- magnetic layer: Co/Pt multilayer
magnetic properties by multilayer structure
→ sensitive to the physical damage
- method: **Grazing Incidence X-ray Reflectivity (GIXR)**
layer structure, roughness



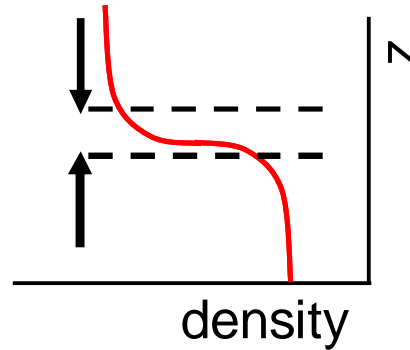
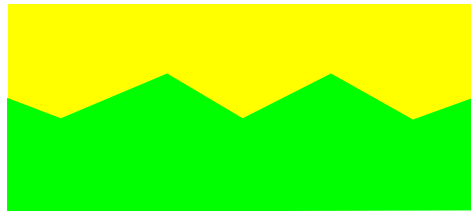
similar refraction is expected;
multilayer: reduced intensity
underlayer: increased intensity
dot edge: scattering

experiment - measurement

- saturation magnetization (M_s): VSM
- magnetic anisotropy energy (K_u): VSM, torque meter
- crystalline structure: XRD
- thickness and roughness: GIXR
- microstructure: TEM



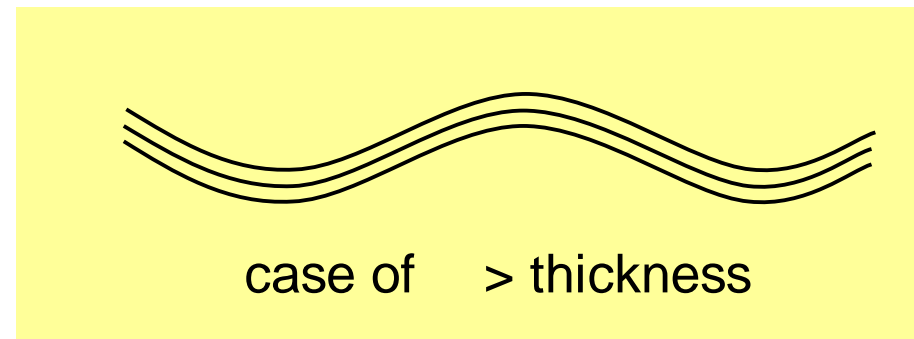
Fitting model; roughness



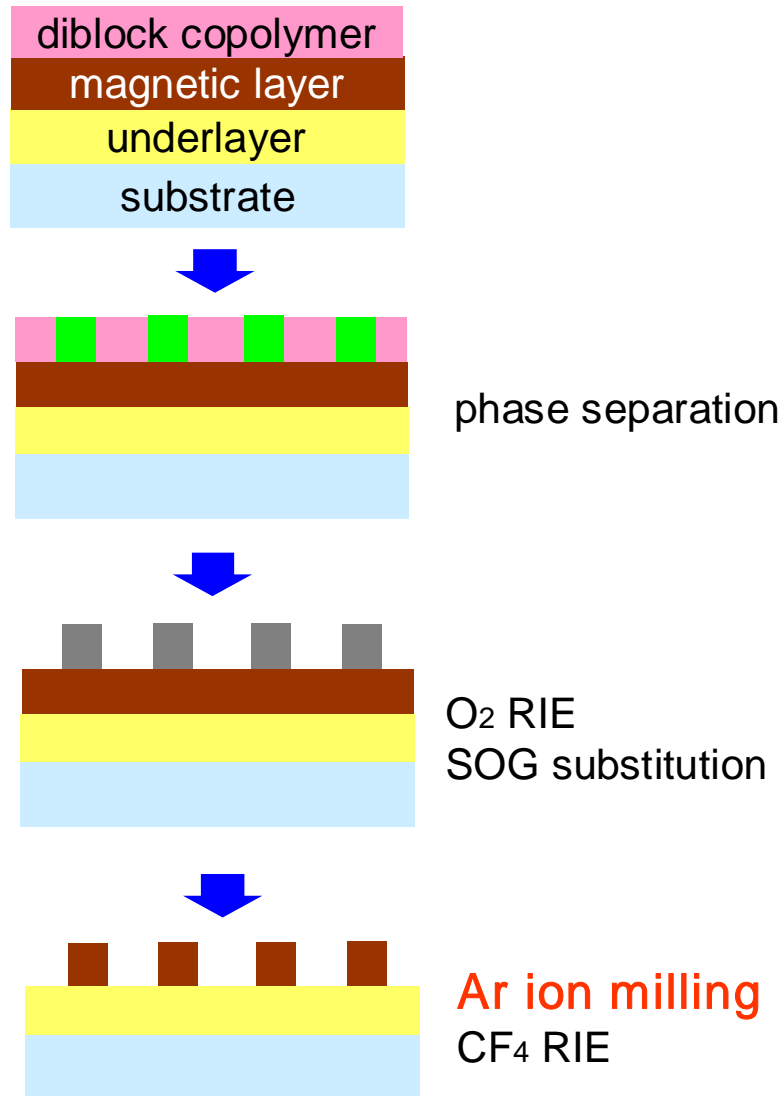
rough interface → gradual density change: $\rho(z)$
 $\rho(z)$: error function

$$\rho(z) = \frac{1}{\sqrt{\pi}} \int_{-\infty}^z \exp\left(-\frac{t^2}{2\sigma^2}\right) \cdot dt$$

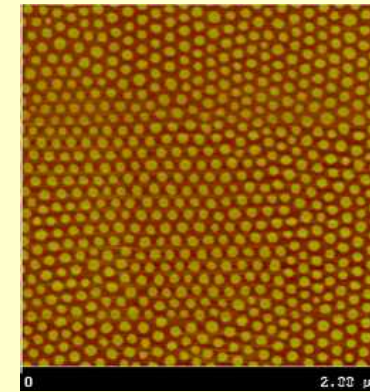
σ : roughness



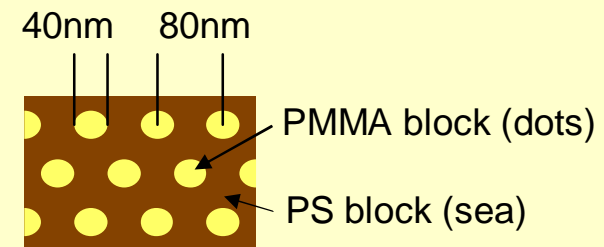
experiment – fabrication process



PS-PMMA diblock copolymer

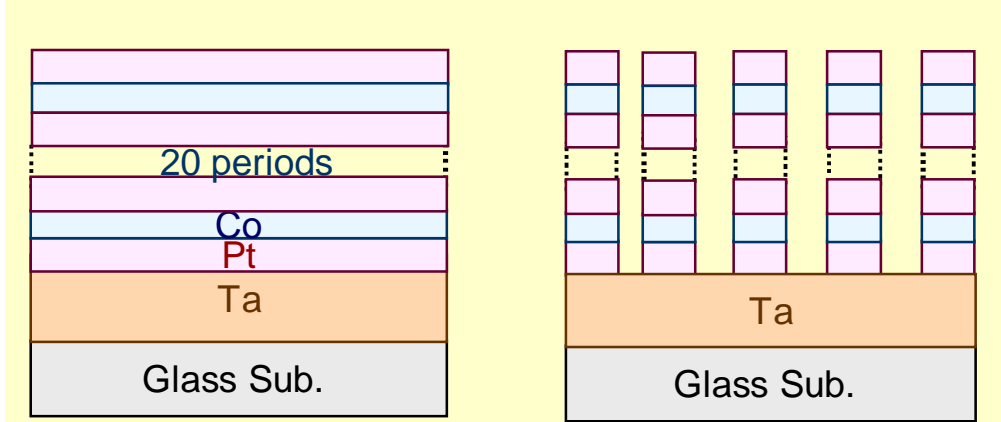
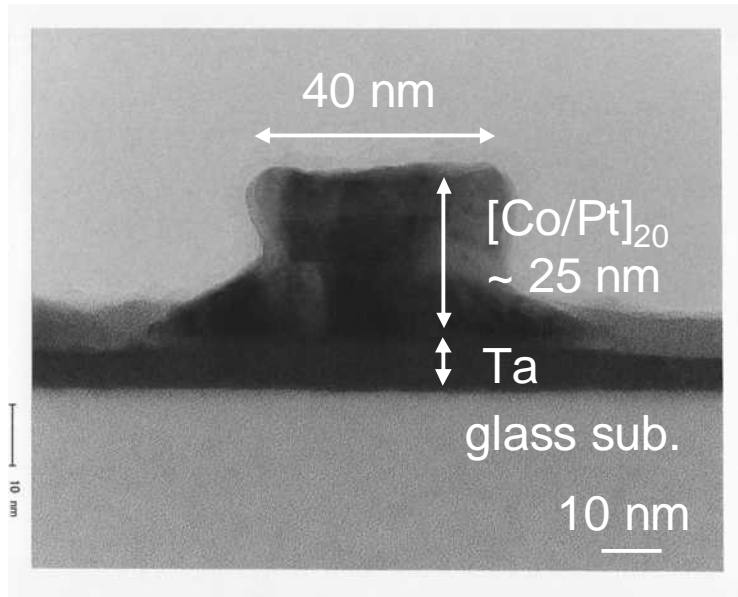
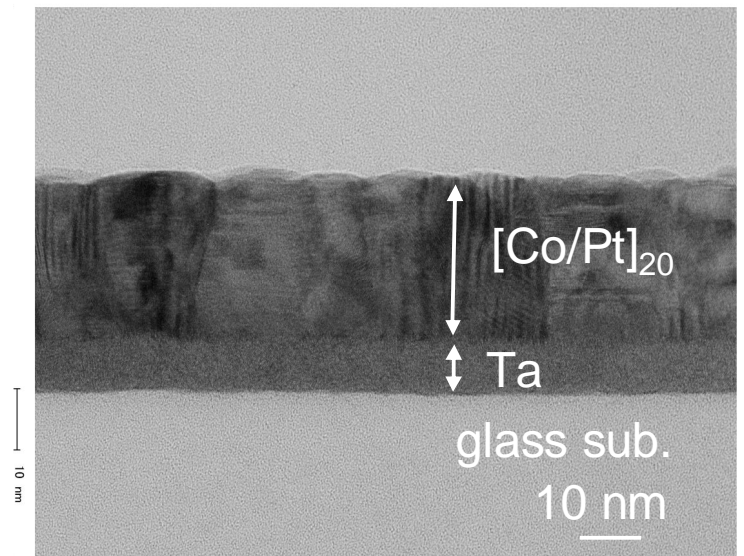


AFM



K. Naito et.al.: IEEE Trans.Magn. 38, 1949 (2002)

Co/Pt multilayer sample

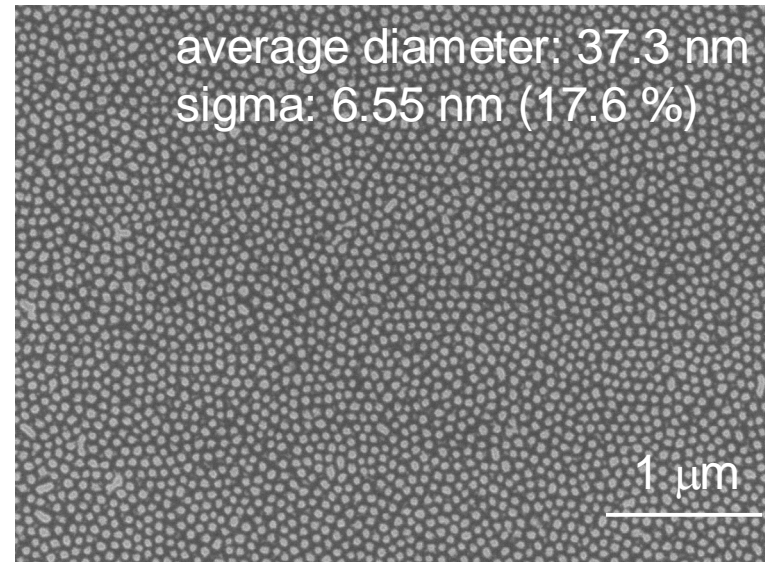
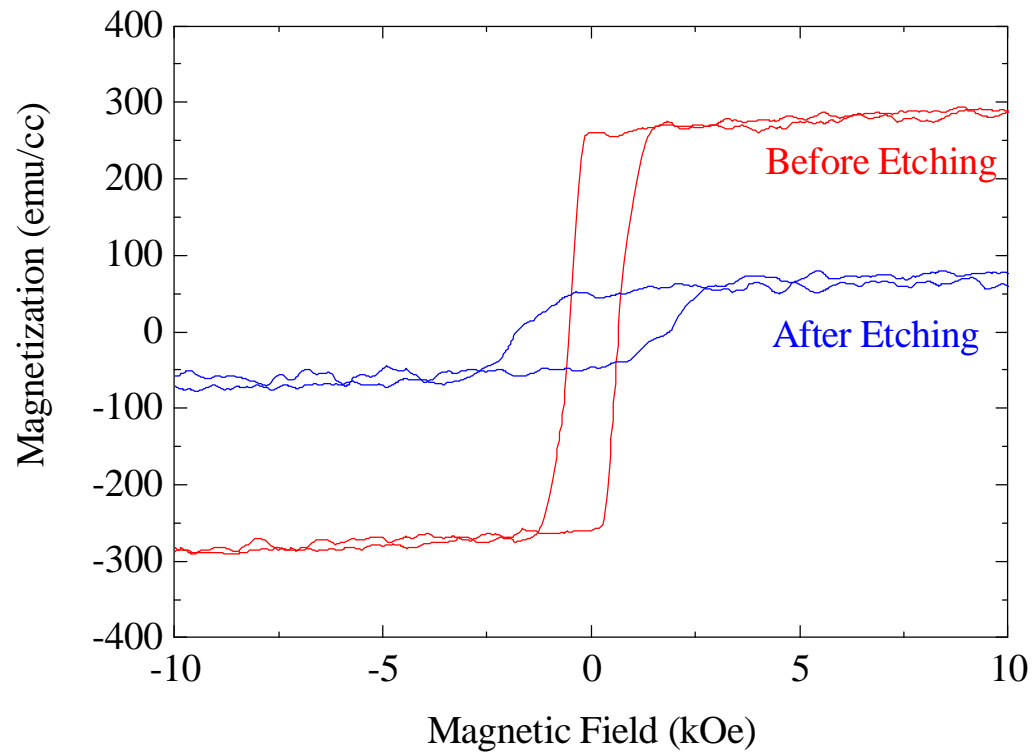


Before Etching

After Etching

- **Sputtering condition**
 - Co: 0.3nm, Pt: 0.9nm
 - DC sputtering
 - no substrate heating
 - Ar pressure: 0.5 Pa
- **Milling condition**
 - substrate cooling
 - accelerating voltage : 400 eV
 - Ar pressure : 2.5X10⁻⁴ Torr
 - etching angle : 30 deg.

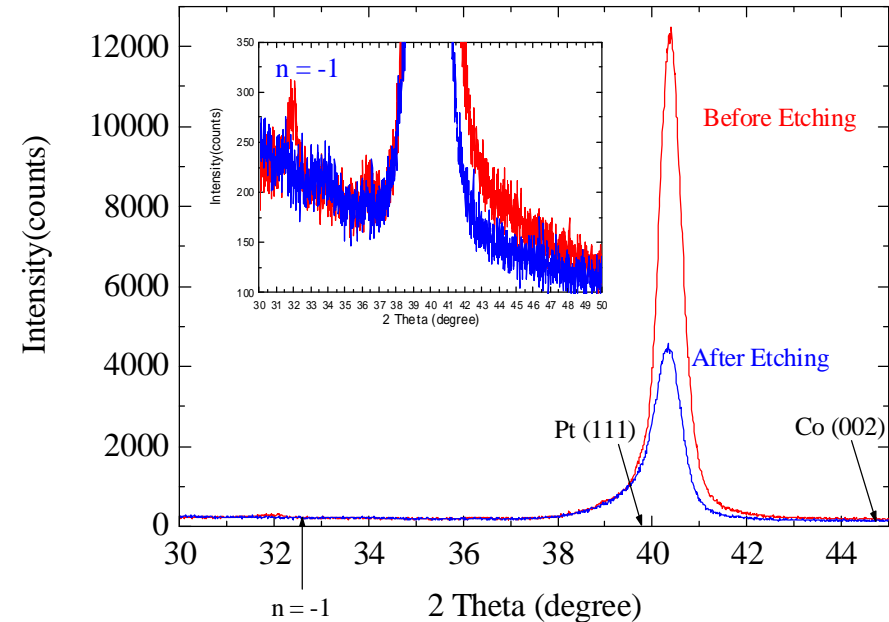
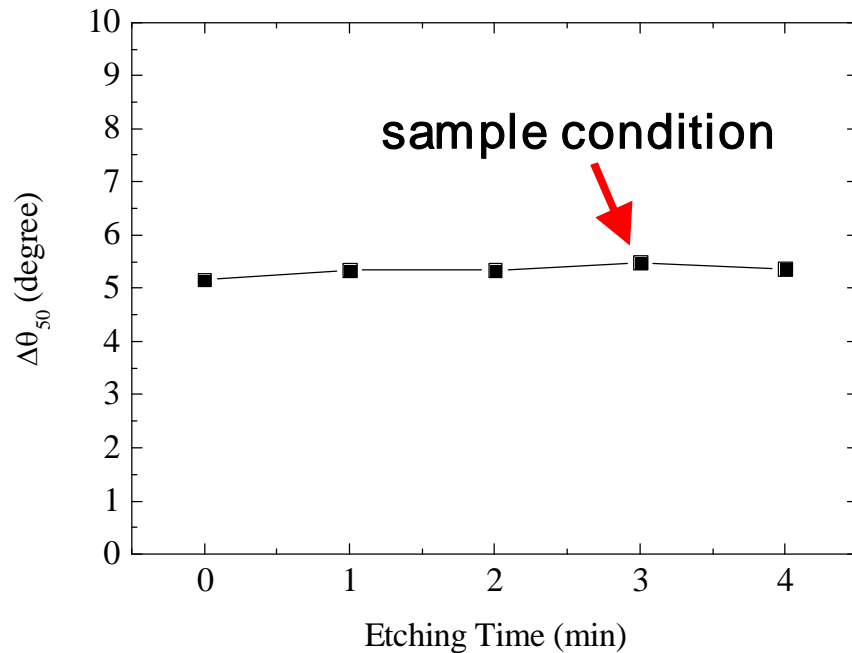
magnetic properties



little damage to the magnetic properties

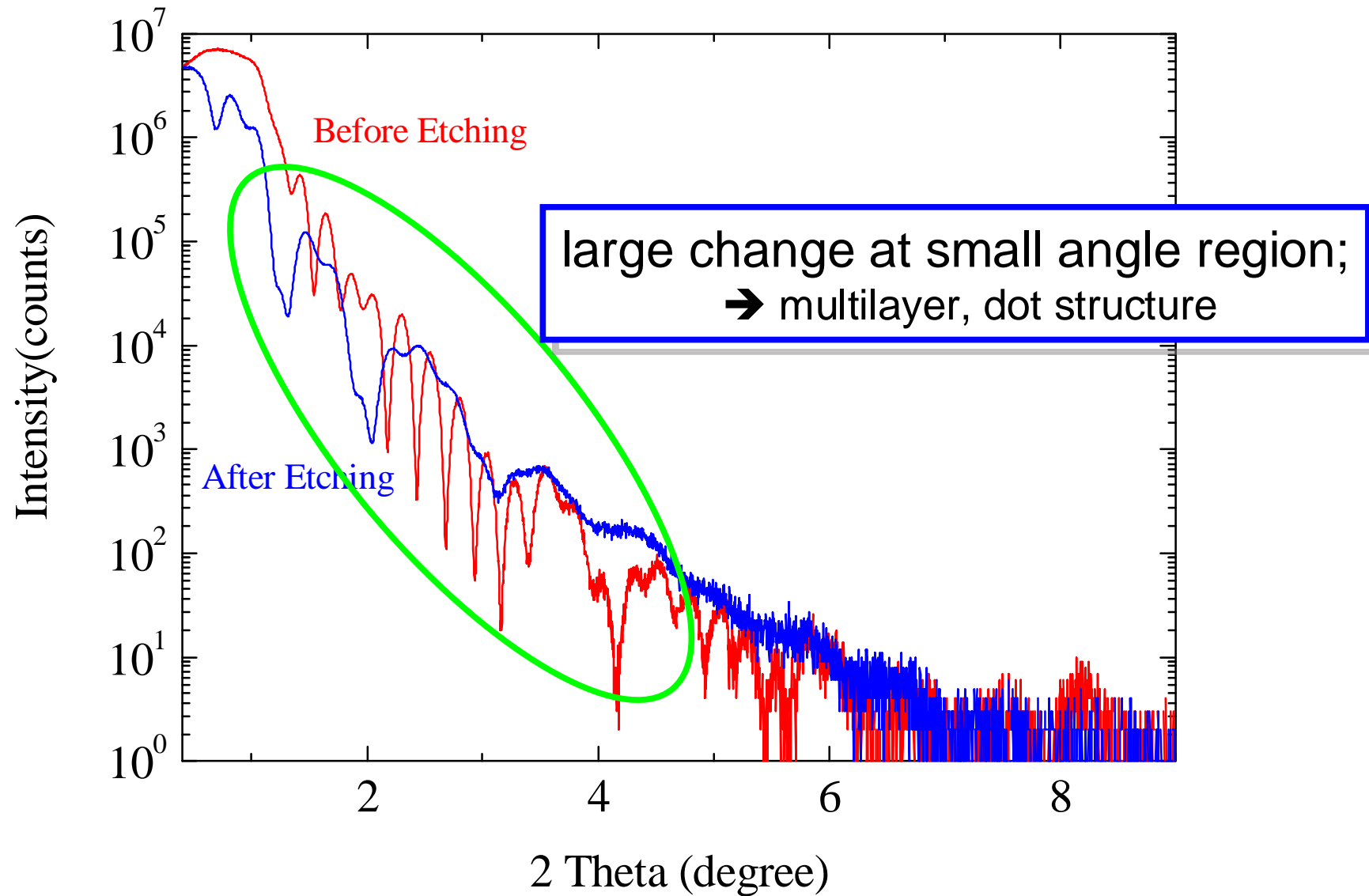
- reduction in M_s : proportional to the packing density
- K_u (by torque curve amplitude): no change

crystal properties (XRD: θ - 2θ)

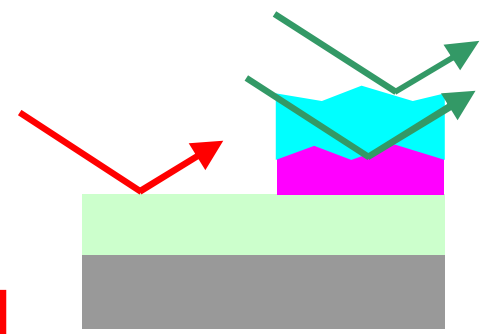
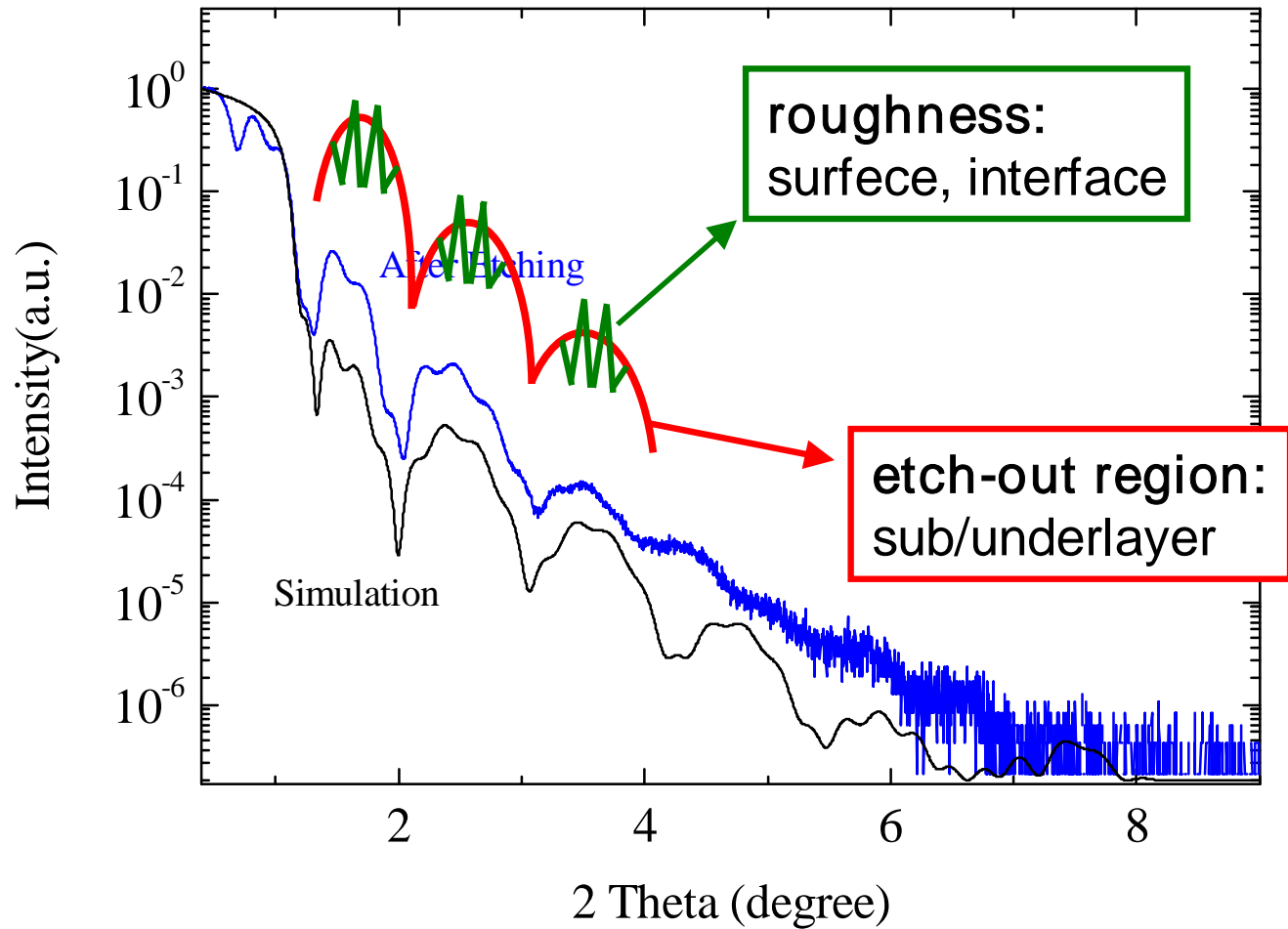


- $\Delta\theta_{50}$: little change throughout the etching process
- θ - 2θ :
 - reduced intensity by volume reduction
 - before etching: satellite peak from multilayer structure
 - **after etching: no satellite peak → damage?**

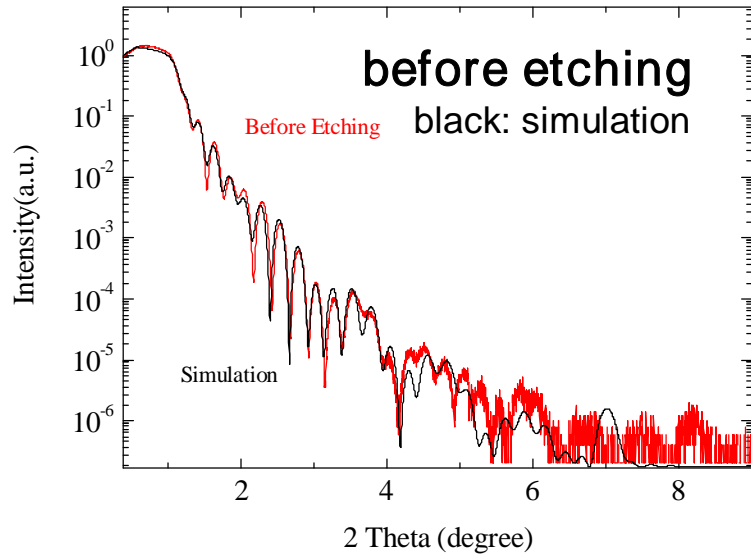
X-ray reflection profile



profile details (after etching)

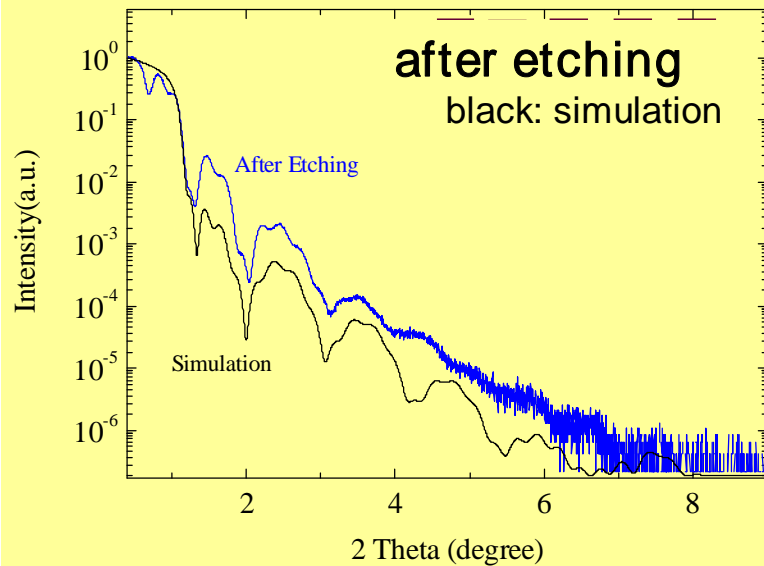


fitting results



	Nominal thickness (nm)	Fitting thickness (nm)	Roughness (nm)
Top Pt	0.9	0.90	0.90
[Co/Pt] ₂₀	0.3/0.9	0.37/0.90	0.45/0.90
Ta	8.0	7.45	0.50
Glass Sub.			0.5

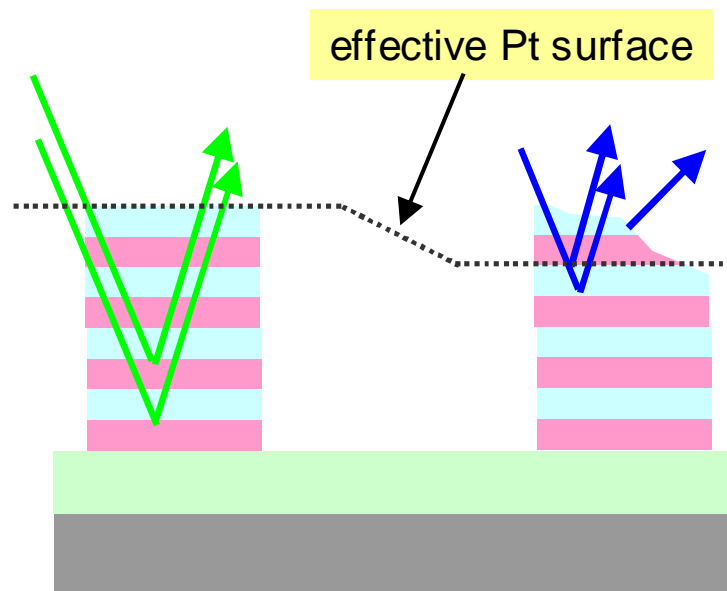
- good agreement with nominal thickness
- roughness ~1nm at [Co/Pt] and top



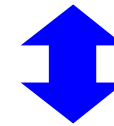
	Nominal thickness (nm)	Fitting thickness (nm)	Roughness (nm)
Top Pt	0.9	0.80	3.80
[Co/Pt] ₂₀	0.3/0.9	0.38/0.80	0.45/0.90
Ta	8.0	7.40	0.55
Glass Sub.			0.5

- little change in ML structure (roughness)
- large roughness at the top Pt layer

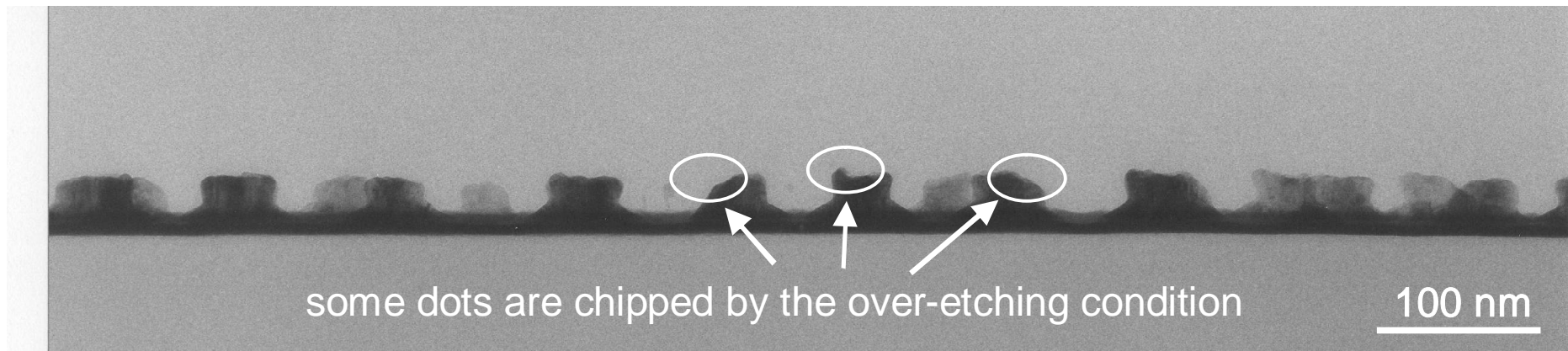
origin of the large surface roughness



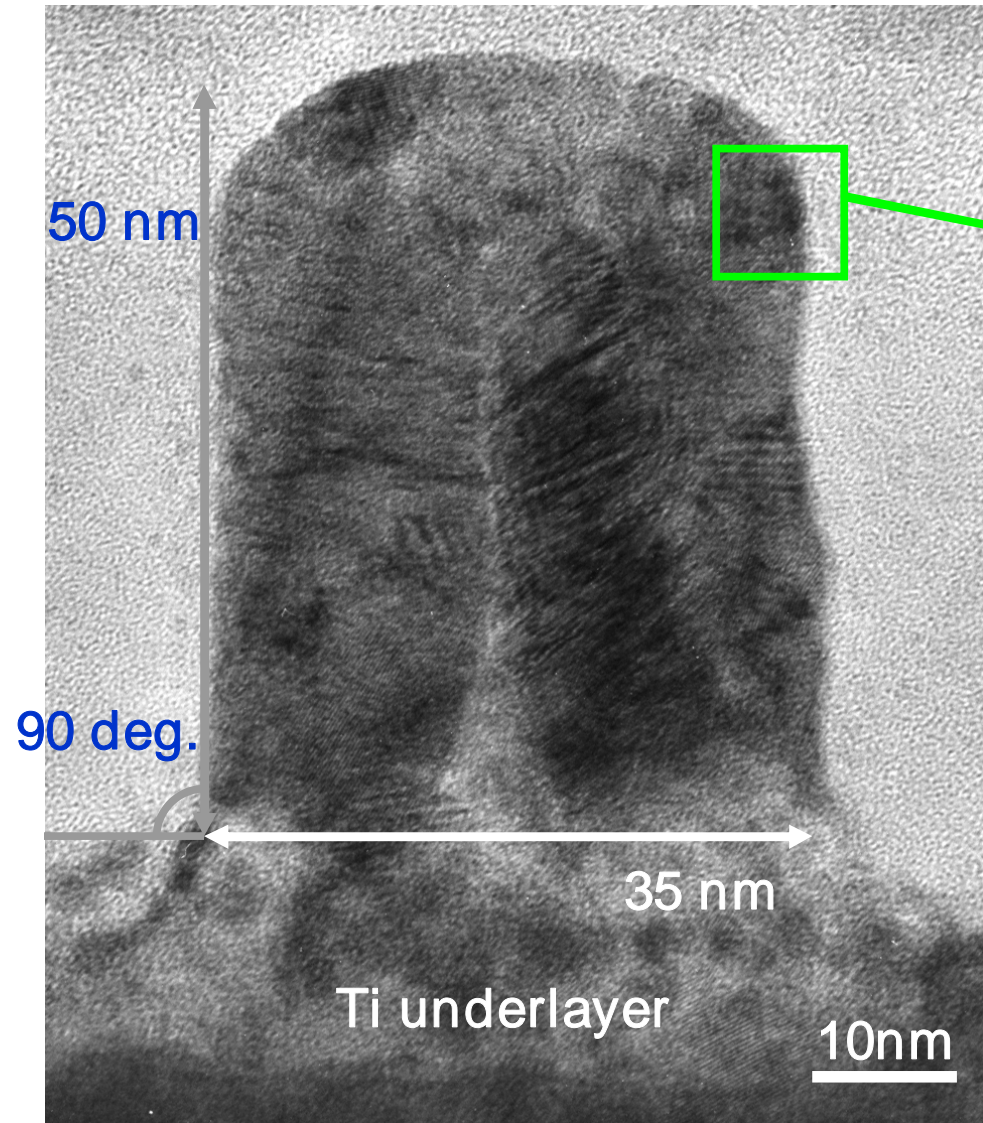
chipped dots
but
smooth ML structure



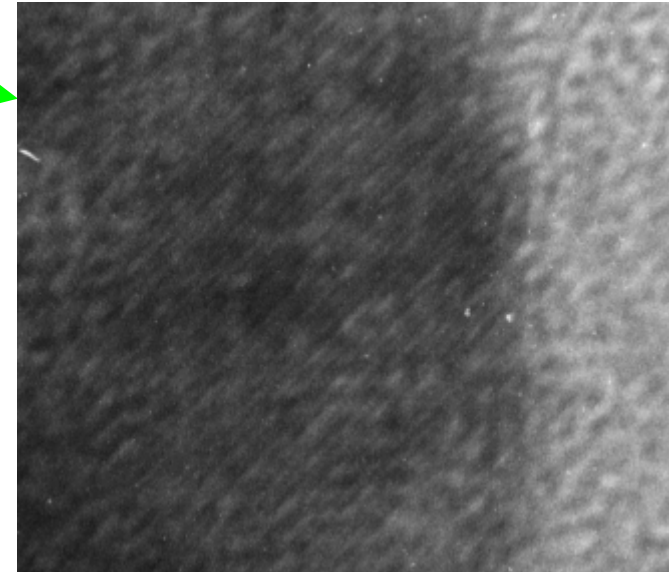
little change in magnetic properties



CoPt合金の例：サイドダメージは少ない



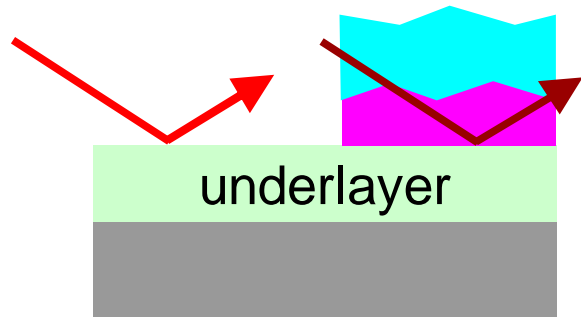
clear crystalline lattice:
no damage



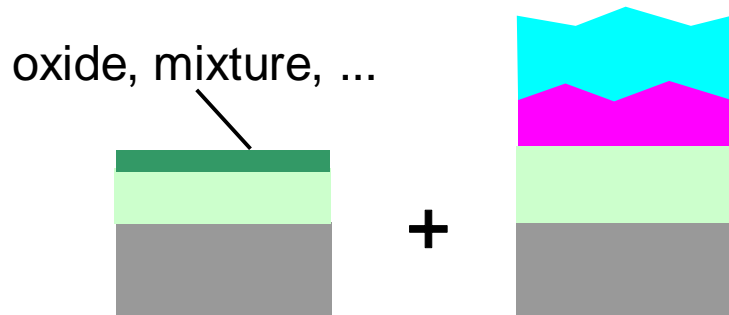
Etching angle : 30 deg.
Etching time : 8 min.

for further precise estimation

Issue: strong reflection from the etched-out region



difference in reflectivity of underlayer between etch-out region and dot region
→ Analytical estimation is difficult.



Summation of two spectra (or subtraction) could work well.

conclusion

Grazing Incidence X-ray reflection method for etching damage analysis of BPM

- **Co/Pt multilayer patterned media:**
 - large surface roughness with smooth ML structure**
chipping by the over-etching condition
smooth ML \Leftrightarrow little damage of magnetic properties
- **ion milling process causes less damage**
- **issues for precise estimation**
;strong reflection from residue underlayer